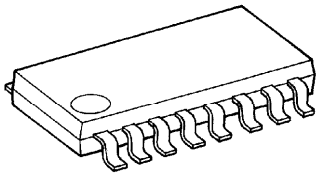
TENTATIVE TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MULTI CHIP

T A 8 3 2 3 F

LOW SATURATION VOLTAGE DRIVER FOR MOTOR

TA8323F is Multi Chip IC incorporates 6 low saturation discrete transistors which equipped bias resistor and free-wheeling diode.
This IC is suitable for a battery use motor drive applications.



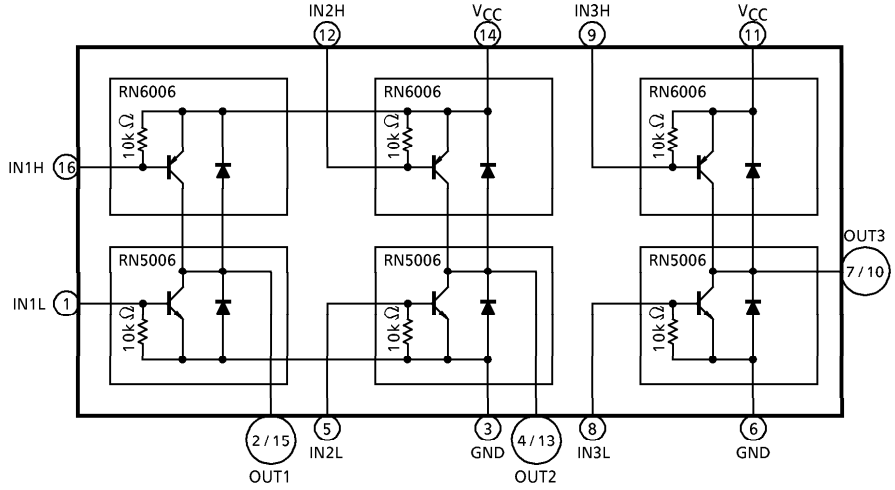
SSOP16-P-225-1.00A

Weight : 0.14g (Typ.)

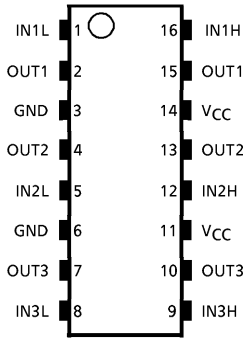
FEATURES

- Suitable for High Efficiency Motor Drive Circuit.
- Built-in Free-Wheeling Diode
- Built-in Bias Resistor : R = 10kΩ
- Small Package sealed : SSOP16
- Low Saturation Voltage

BLOCK DIAGRAM



PIN CONNECTION



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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	10	V
Breakdown Voltage	V_{CBO}	10	V
	V_{CEO}	10	V
	V_{EBO}	6	V
Output Current	I_O	2	A
	$I_{O\ (peak)}$	4 (Note 1)	
Base Current	I_B	±0.4	A
	$I_{B\ (peak)}$	±0.8 (Note 1)	
Diode Forward Current	I_F	2 (Note 2)	A
Power Dissipation	P_D	490	mW
Junction Temperature	T_j	150	°C
Operating Temperature	T_{opr}	−40~85	°C
Storage Temperature	T_{stg}	−55~150	°C

(Note 1) T = 10ms Max. and maximum duty is less than 30%
(Note 2) T = 10ms single pulse

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain		$h_{FE\ (1)}$	—	V_{CE} = 1V, I_C = 0.5A	160	—	600	
		$h_{FE\ (2)}$	—	V_{CE} = 1V, I_C = 2.0A	60	130	—	
Saturation Voltage	Upper Side	$V_{CE\ (sat)}$	—	I_C = 1A, I_B = 25mA	—	0.16	0.22	V
				I_C = 2A, I_B = 50mA	—	0.28	0.45	
	Lower Side			I_C = 1A, I_B = 25mA	—	0.13	0.32	
				I_C = 2A, I_B = 50mA	—	0.25	0.45	
	Summing Total			I_C = 1A, I_B = 25mA	—	0.29	0.52	
				I_C = 2A, I_B = 50mA	—	0.53	0.85	
Transition Frequency		f_T	—	V_{CE} = 2V, I_C = 0.5A	—	150	—	MHz
Leakage Current	Upper Side	I_{OL}	—	V_{CC} = 10V	—	0	5	μA
	Lower Side			V_{CC} = 10V	—	0	5	
Diode Forward Voltage	Upper Side	V_F	—	I_F = 300mA	—	0.89	1.2	V
				I_F = 450mA 10ms Pulse measure	—	1.60	—	
	Lower Side			I_F = 300mA	—	0.89	1.2	
				I_F = 450mA 10ms Pulse measure	—	1.60	—	
Base-Emitter Resistance		R_{BE}	—		7	10	13	kΩ
Base-Emitter Forward Voltage		$V_{BE\ (PNP)}$	—	V_{CE} = −1V, I_C = 2A	—	0.84	1.5	V
		$V_{BE\ (NPN)}$	—	V_{CE} = 1V, I_C = 2A	—	0.84	1.5	

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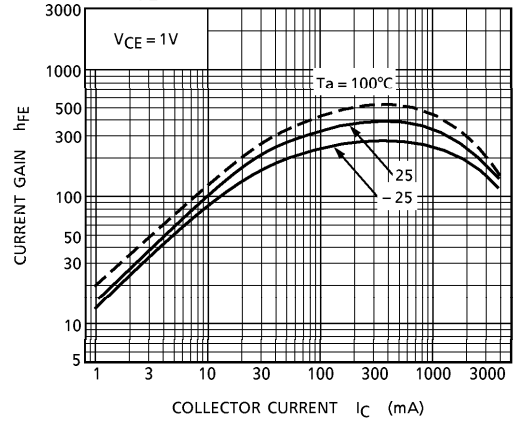
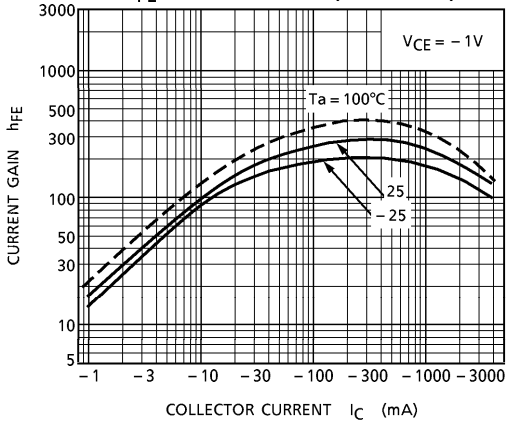
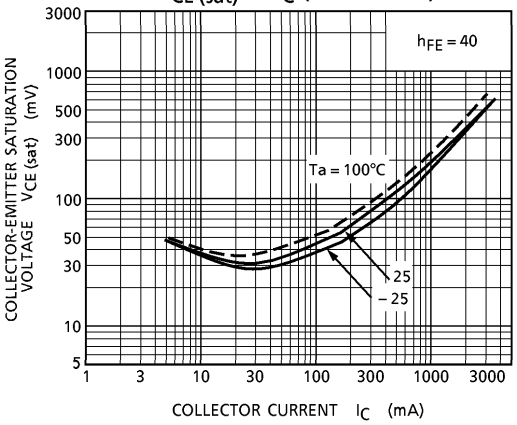
TRANSISTOR (RN5006)
h_{FE} CHARACTERISTIC (LOWER SIDE)



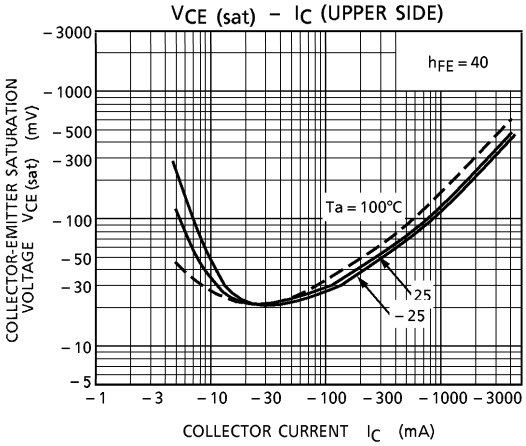
TRANSISTOR (RN6006)
h_{FE} CHARACTERISTIC (UPPER SIDE)



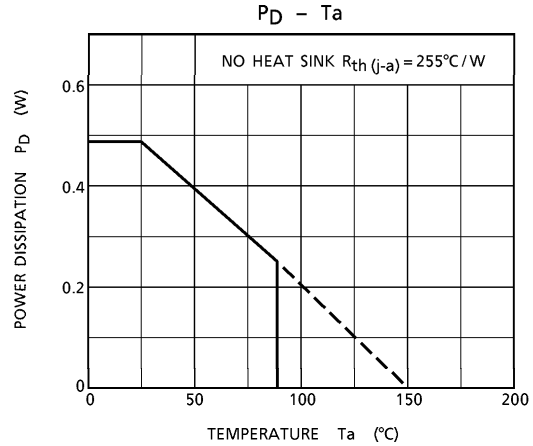
TRANSISTOR (RN5006)
$V_{CE\,(sat)}$ – I_C (LOWER SIDE)



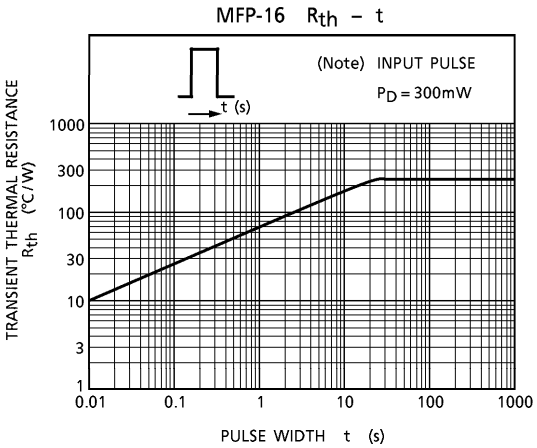
TRANSISTOR (RN6006)
$V_{CE\,(sat)}$ – I_C (UPPER SIDE)



P_D – Ta



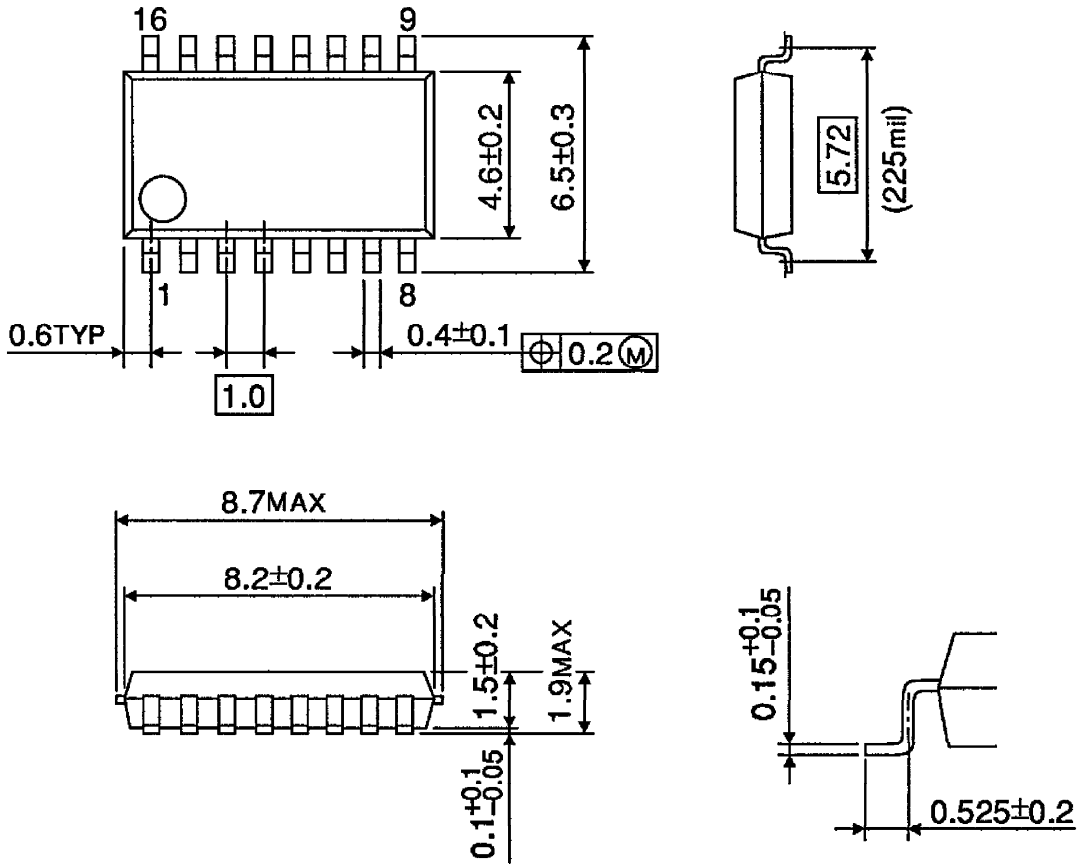
MFP-16 R_{th} – t



OUTLINE DRAWING

SSOP16-P-225-1.00A

Unit : mm



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